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U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

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FILING DATE
August 19, 2003

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5174

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

SEP 30 2003

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TIN	6,025,261	2/2000	Farrar et al.	438	619	
	6,083,802 -	7/2000	Wen et al.	438	381	
	6,107,893	8/2000	Forbes	331	132	· · ·
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	6,239,684	5/2001	Farrar et al.	336	200	
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						YES	NO

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